Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection: 2 kV HBM
- Ultra thin package profile of 0.37 mm

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | 20 | V |
| V _{GS} | gate-source voltage | | | -8 | - | 8 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | - | 1.5 | Α |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 4.5 \text{ V}; I_D = 1.5 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | | - | 170 | 200 | mΩ |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1 | G | gate | 1 🔲 | D I |
| 2 | S | source | 2 3 | |
| 3 | D | drain | Transparent top view DFN1006B-3 (SOT883B) | G S 017aaa255 |

6. Ordering information

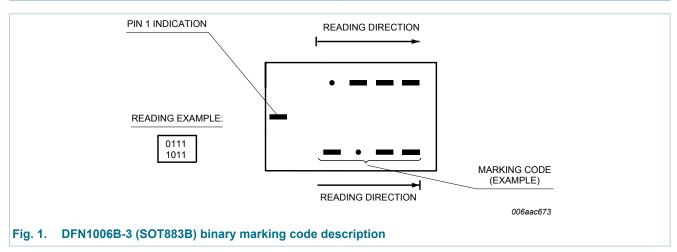
Table 3. Ordering information

| Type number | Package | | | | |
|-------------|------------|--|---------|--|--|
| | Name | Description | Version | | |
| PMZB150UNE | DFN1006B-3 | DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm | SOT883B | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMZB150UNE | 0101 0000 |



8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 20 | V |
| V_{GS} | gate-source voltage | | | -8 | 8 | V |
| I _D | drain current | V_{GS} = 4.5 V; T_{amb} = 25 °C | [1] | - | 1.5 | Α |
| | | V _{GS} = 4.5 V; T _{amb} = 100 °C | [1] | - | 1 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | 6 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 350 | mW |
| | | | [1] | - | 760 | mW |
| | | T _{sp} = 25 °C | | - | 6250 | mW |
| T _j | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | in diode | | | , | ' | , |
| Is | source current | T _{amb} = 25 °C | [1] | - | 0.7 | Α |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

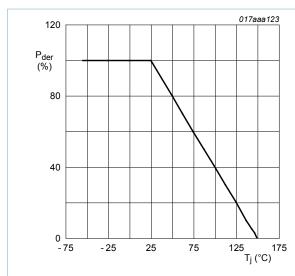


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

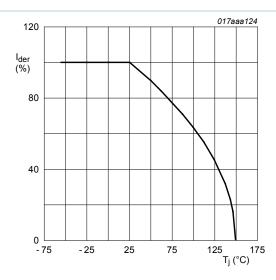


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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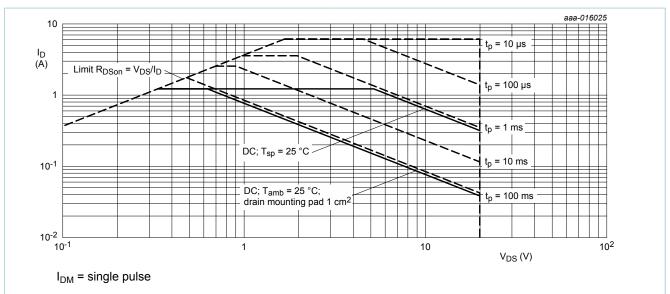


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| froi | thermal resistance in from junction to ambient | | [1] | - | 315 | 360 | K/W |
| | | | [2] | - | 145 | 165 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 17 | 20 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

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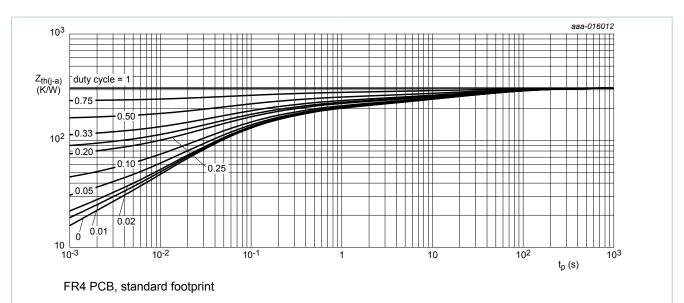
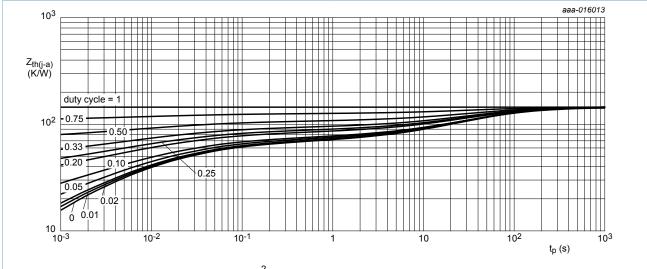


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7 Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|--|------|------|------|------|
| Static chara | acteristics | | ' | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 0.45 | 0.7 | 0.95 | V |
| I _{DSS} | drain leakage current | V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 5 | μA |
| | | V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -5 | μA |
| | | V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 1 | μA |
| | | V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -1 | μA |
| | | V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| | | V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -100 | nA |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 4.5 V; I_D = 1.5 A; T_j = 25 °C | - | 170 | 200 | mΩ |
| re | | V _{GS} = 4.5 V; I _D = 1.5 A; T _j = 150 °C | - | 230 | 280 | mΩ |
| | | V_{GS} = 2.5 V; I_D = 1.4 A; T_j = 25 °C | - | 200 | 270 | mΩ |
| | | V_{GS} = 1.8 V; I_D = 0.25 A; T_j = 25 °C | - | 240 | 340 | mΩ |
| | | V_{GS} = 1.5 V; I_D = 0.01 A; T_j = 25 °C | - | 300 | 570 | mΩ |
| 9 _{fs} | forward transconductance | V _{DS} = 10 V; I _D = 1.2 A; T _j = 25 °C | - | 3.5 | - | S |
| Dynamic ch | naracteristics | | | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 10 V; I _D = 1.6 A; V _{GS} = 4.5 V; | - | 1.6 | - | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 0.15 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.44 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V; | - | 93 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 18 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 16 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = 10 V; I _D = 1.6 A; V _{GS} = 4.5 V; | - | 5.3 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 12 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 16 | - | ns |
| t _f | fall time | | - | 5 | - | ns |
| Source-dra | in diode | | ' | | | , |
| V_{SD} | source-drain voltage | $I_S = 0.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 0.8 | 1.2 | V |

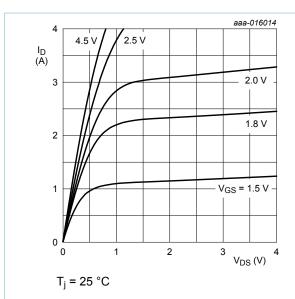
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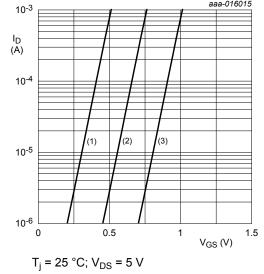
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aaa-016015



Output characteristics: drain current as a Fig. 7. function of drain-source voltage; typical values



- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage

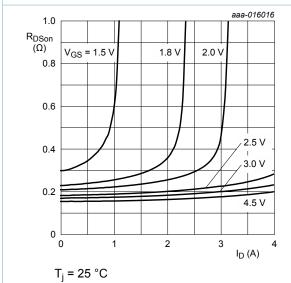
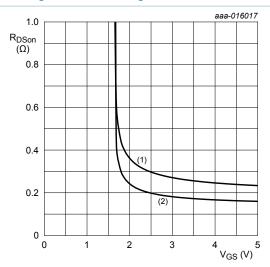


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 0.2 A$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

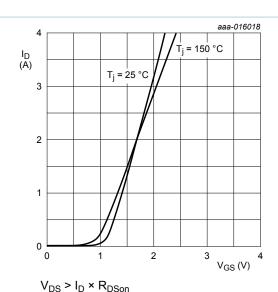


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

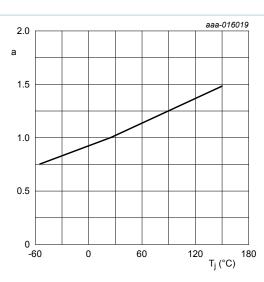
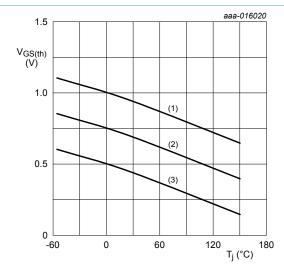


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

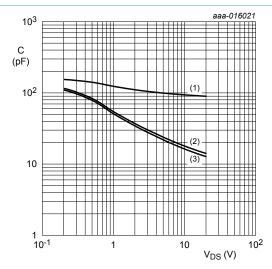
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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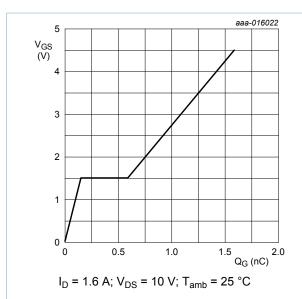


Fig. 15. Gate-source voltage as a function of gate charge; typical values

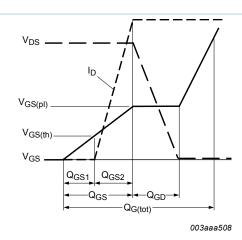
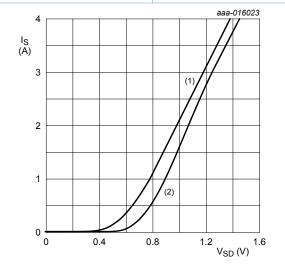


Fig. 16. MOSFET transistor: Gate charge waveform definitions

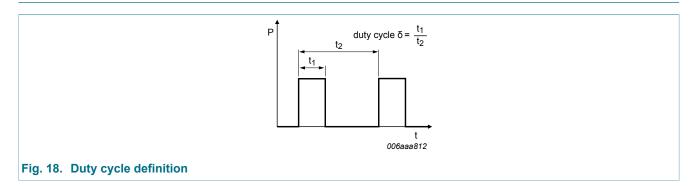


 $V_{GS} = 0 V$ (1) $T_j = 150 °C$ (2) $T_i = 25 °C$

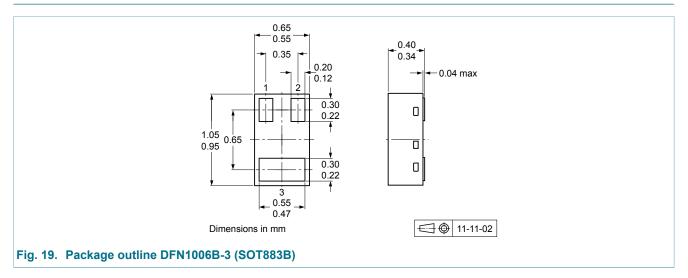
Fig. 17. Source current as a function of source-drain voltage; typical values

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11. Test information



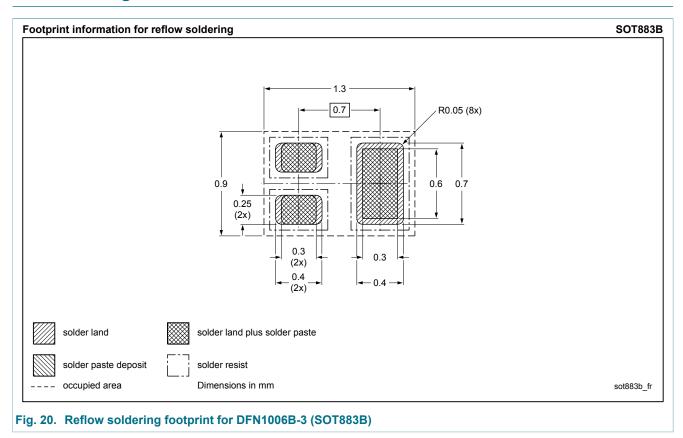
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMZB150UNE v.1 | 20150324 | Product data sheet | - | - |

15. Legal information

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|--------------------------------------|--------------------|---|
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